



GP
ELECTRONICS

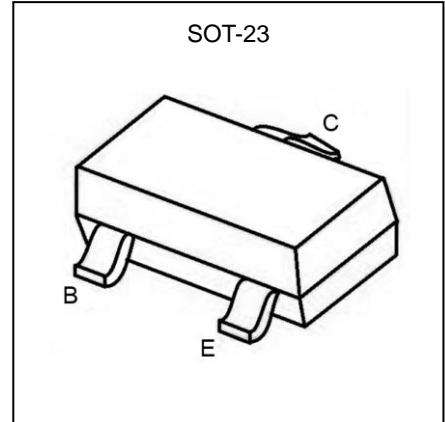
MMBT4403

MMBT4403 Transistor(PNP)

Feature

- Small Surface Mount Package

Marking: 2T



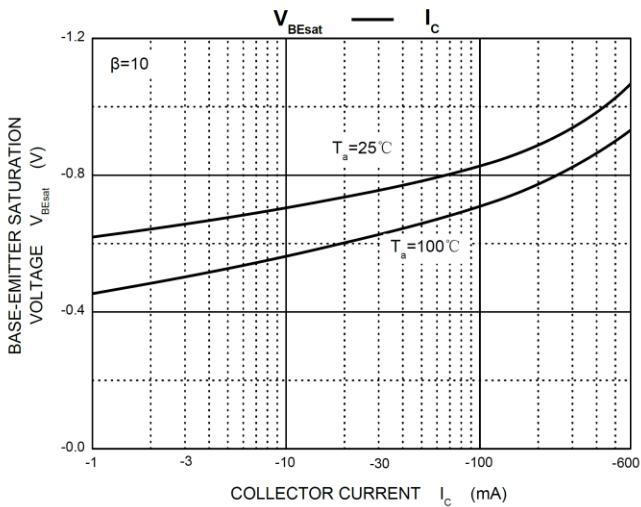
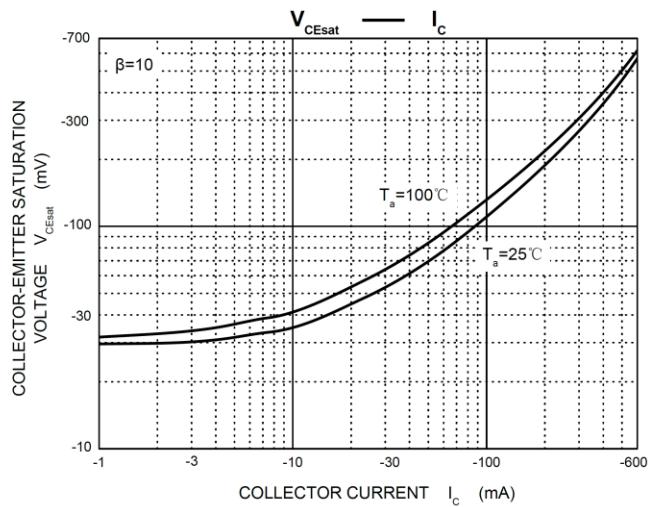
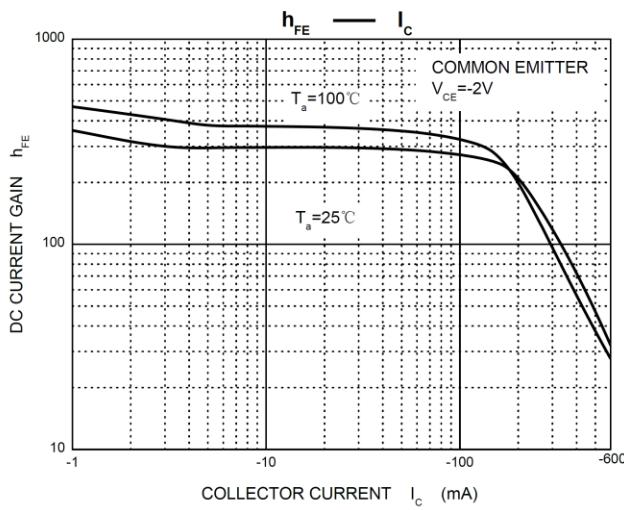
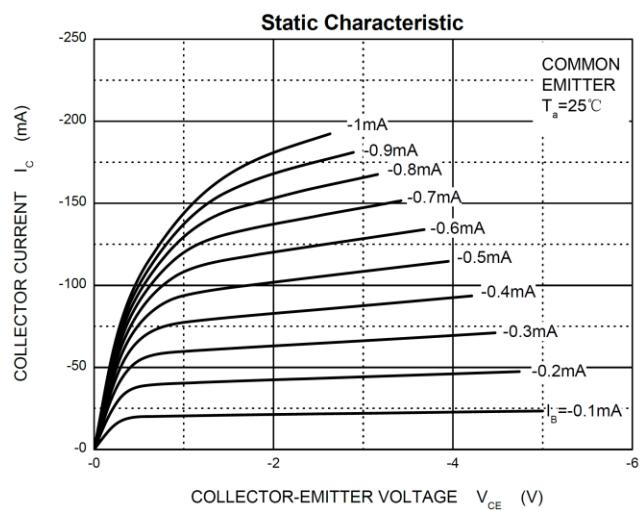
MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

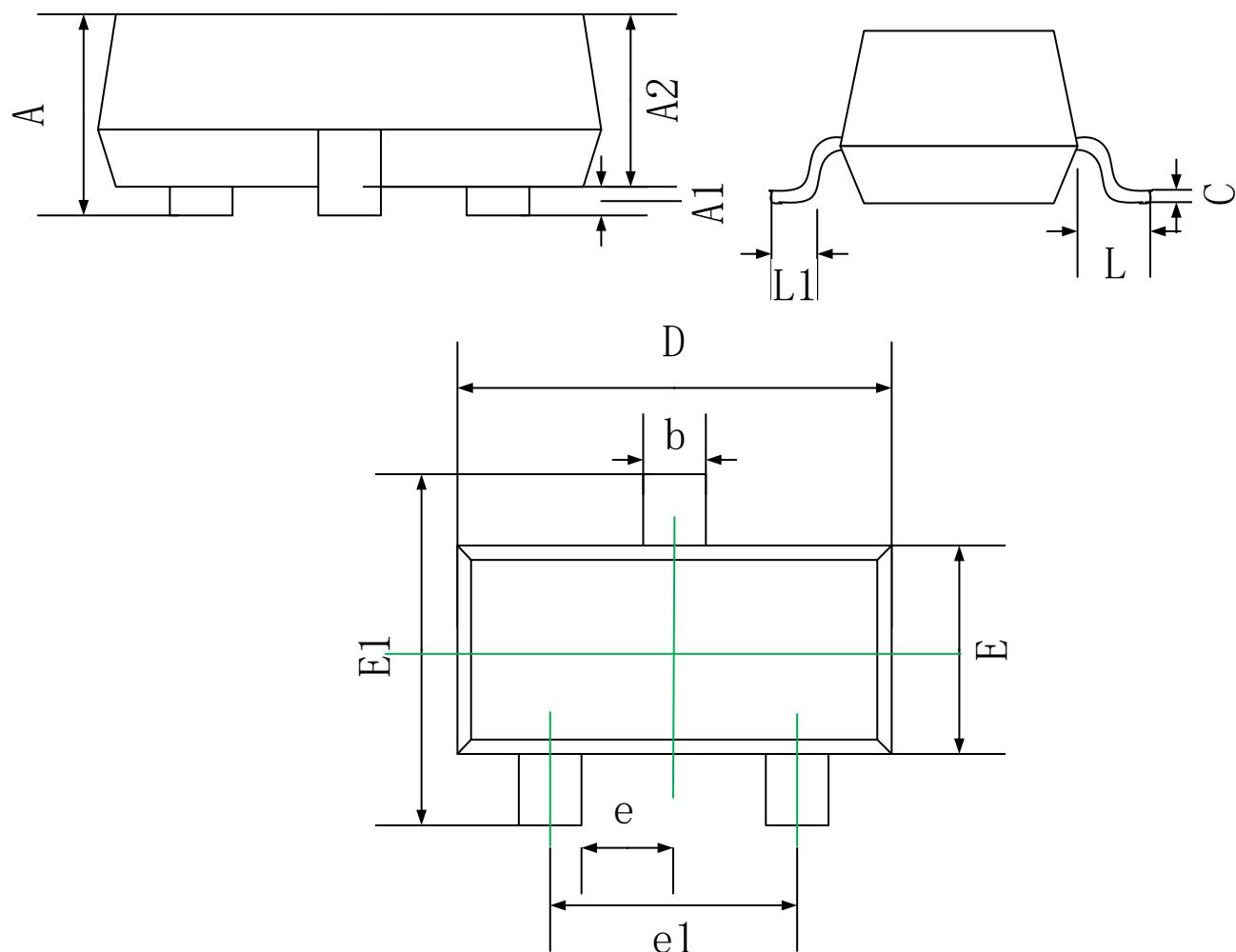
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-0.6	A
Power Dissipation	P_d	0.3	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_E=0$	-40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}, I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-35\text{V}, I_E=0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-35\text{V}, V_{BE}=0.4\text{V}$		-0.1	μA
Emitter-base cut-off current	I_{EBO}	$V_{EB}=-4\text{V}, I_C=0$		-0.1	μA
DC current gain	h_{FE1}	$V_{CE}=-1\text{V}, I_C=-0.1\text{mA}$	30		
	h_{FE2}	$V_{CE}=-1\text{V}, I_C=-1\text{mA}$	60		
	h_{FE3}	$V_{CE}=-1\text{V}, I_C=-10\text{mA}$	100		
	h_{FE4}	$V_{CE}=-2\text{V}, I_C=-150\text{mA}$	100	300	
	h_{FE5}	$V_{CE}=-2\text{V}, I_C=-500\text{mA}$	20		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$		-0.75	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$		-1.3	V
Transition frequency	f_T	$V_{CE}=-10\text{V}, I_C=-20\text{mA}, f=100\text{MHz}$	200		MHZ

Typical Characteristics



SOT-23 Package Information


Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50